



#21G
12-27-2
Robertson
amdt

0039-7684-2SRD DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

Hisako AOYAMA et al.

SERIAL NO.: 09/558,053

CPA FILED: July 8, 2002

FOR: PROCESS FOR FABRICATING
A METAL WIRING AND METAL
CONTACT IN A SEMICONDUCTOR
DEVICE

:

: GROUP ART UNIT: 2823

:

: EXAMINER: Julio J. MALDONADO

:

ext 6211

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office Action dated August 30, 2002, please amend the above-

identified application as follows:

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DEC-6 2002
TECHNOLOGY CENTER 2800

IN THE CLAIMS

Please amend the claims as shown in the marked-up copy to read as follows:

29. (Four Times Amended) A process of fabricating a semiconductor device comprising the steps of:

- forming a first insulating film on a semiconductor substrate;
- forming a second insulating film on said first insulating film, said second insulating film being made of a material different from that of the first insulating film and having a thickness smaller than that of the first insulating film;

Not responsive
do not
enter
(3/27/03)

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Paul
H-1